

APPLICATIONS FveTw [( s).6(e Tw [( F)0(coveTw [( ygedness)]TJ /TT5 1 Tf -10.3571-2.0714 TD 0 Tc 0 Tw <01b6>Tj /TT4

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# MMG200D170B

IGBT-inverter

ELECTRICAL CHARACTERISTICS

Unit

mA

mA

nA

$\mu$ C

nF

nF

ns

ns

ns

ns

ns

ns

ns

ns



MMG200D170B

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$I_F(A)$

$E_{REC}(mJ)$

$V_{FD}$

Figure 9. Diode Forward Characteristics Diode -inverter

$R_g \text{ } \mu s$

Figure 10. Switching Energy vs Gate Resiste

Figure 13. Circuit Diagram